

Abstract of the Disclosure

A semiconductor memory device includes a semiconductor substrate, and gate electrodes formed
5 for a transistor on the semiconductor substrate through a gate insulating film. A gate length of the gate electrode is longer than a minimum processing dimension. The semiconductor memory device may further include a first diffusion layer formed in a
10 surface of the semiconductor substrate to function as one of a source and a drain, and a second diffusion layer formed in the surface of the semiconductor substrate to function as the other of the source and the drain. The shortest distance between the first
15 diffusion layer and the second diffusion layer is proportional to the gate length. In this case, the semiconductor memory device may further include a gate insulating film formed on the semiconductor substrate and extending over the first diffusion layer and the
20 second diffusion layer. The gate electrode is formed on the gate insulating film.